## **CLAIMS**

- 1. A thick film photoresist composition comprising:
- (A) a resin component containing (a) from 61 to 90% by weight of a structural
   unit derived from a cyclic alkyl (meth)acrylate ester, and (b) a structural unit derived
   from a radical polymerizable compound containing a hydroxyl group,
  - (B) a polymerizable compound containing at least one ethylenic unsaturated double bond,
    - (C) a photopolymerization initiator, and
- 10 (D) an organic solvent.
  - 2. A thick film photoresist composition according to claim 1, wherein said structural unit (b) accounts for at least 1% by weight, but less than 10% by weight, of said component (A).

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3. A thick film photoresist composition according to claim 1, wherein said component (A) further comprises (c) a structural unit derived from a radical polymerizable compound represented by a general formula (1) shown below:

$$CH_2 = C$$
 $CH_2 = CH_2$ 
 $CH_$ 

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(wherein, R<sup>1</sup> represents a hydrogen atom or a methyl group, and R<sup>2</sup> represents a hydrogen atom or an alkyl group of 1 to 4 carbon atoms).

- 4. A thick film photoresist composition according to claim 1, wherein said

  component (D) is at least one solvent selected from a group consisting of methyl isobutyl ketone and methyl ethyl ketone.
  - 5. A method of forming a resist pattern, wherein said resist pattern is formed using a thick film photoresist composition according to any one of claim 1 through claim 4.

6. A pattern formed using said method disclosed in claim 5.

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